

# **Amplifier Transistors**

## **NPN Silicon**

## MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

#### **Features**

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



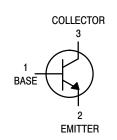
Rating	Symbol	6428LT1	6429LT1	Unit
Collector - Emitter Voltage	$V_{CEO}$	50	45	Vdc
Collector - Base Voltage	$V_{CBO}$	60	55	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	6.0		Vdc
Collector Current - Continuous	Ic	200		mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C	P <sub>D</sub>	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

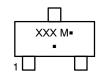
- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.





SOT-23 (TO-236) CASE 318 STYLE 6

#### **MARKING DIAGRAM**



XXX = Specific Device Code MMBT6428LT1 - 1KM NSV/MMBT6429LT1 - M1L

M = Date Code\*■ = Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may

vary depending upon manufacturing location.

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBT6428LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
MMBT6429LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
NSVMMBT6429LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$ $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MMBT6428 MMBT6429 / NSVMMBT6429	V <sub>(BR)CEO</sub>	50 45	- -	Vdc
Collector – Base Breakdown Voltage ( $I_C = 0.1 \text{ mAdc}, I_E = 0$ ) ( $I_C = 0.1 \text{ mAdc}, I_E = 0$ )	MMBT6428 MMBT6429 / NSVMMBT6429	V <sub>(BR)CBO</sub>	60 55	- -	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc)		I <sub>CES</sub>	-	0.1	μAdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)		I <sub>CBO</sub>	-	0.01	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 5.0 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	-	0.01	μAdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 0.01 mAdc, V <sub>CE</sub> = 5.0 Vdc)	MMBT6428 MMBT6429 / NSVMMBT6429	h <sub>FE</sub>	250 500	- -	-
$(I_C = 0.1 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT6428 MMBT6429 / NSVMMBT6429		250 500	650 1250	
$(I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT6428 MMBT6429 / NSVMMBT6429		250 500	- -	
( $I_C$ = 10 mAdc, $V_{CE}$ = 5.0 Vdc)	MMBT6428 MMBT6429 / NSVMMBT6429		250 500	- -	
Collector – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 0.5 \text{ mAdc}$ ) ( $I_C = 100 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )		V <sub>CE(sat)</sub>	- -	0.2 0.6	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc)		V <sub>BE(on)</sub>	0.56	0.66	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)		f <sub>T</sub>	100	700	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		$C_{ m obo}$	-	3.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ibo</sub>	-	8.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

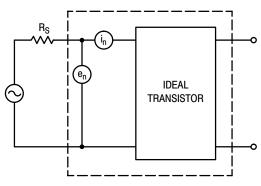


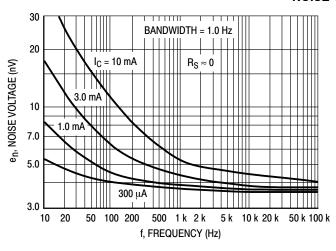
Figure 1. Transistor Noise Model

### MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

#### **NOISE CHARACTERISTICS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$ 

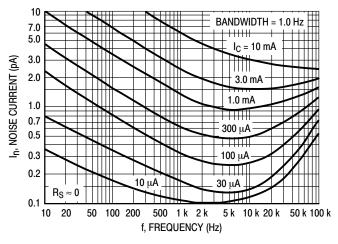
#### **NOISE VOLTAGE**



BANDWIDTH = 1.0 Hz 20 en, NOISE VOLTAGE (nV)  $R_S \approx 0\,$ f = 10 Hz 10 100 Hz 7.0 1.0 kHz 5.0 3.0 0.02 0.01 0.05 0.1 0.2 0.5 1.0 5.0 10 IC, COLLECTOR CURRENT (mA)

Figure 2. Effects of Frequency

Figure 3. Effects of Collector Current



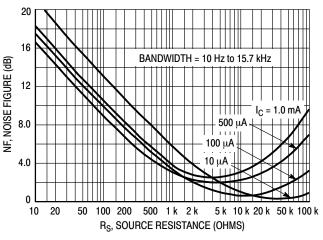
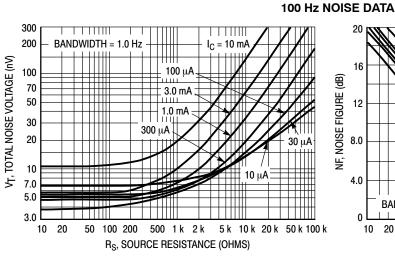


Figure 4. Noise Current

Figure 5. Wideband Noise Figure



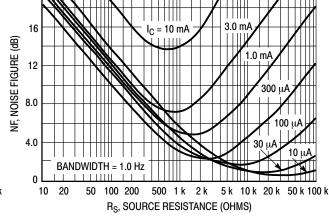


Figure 6. Total Noise Voltage

Figure 7. Noise Figure

## MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

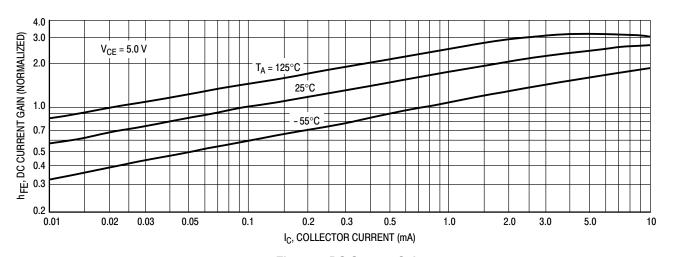


Figure 8. DC Current Gain

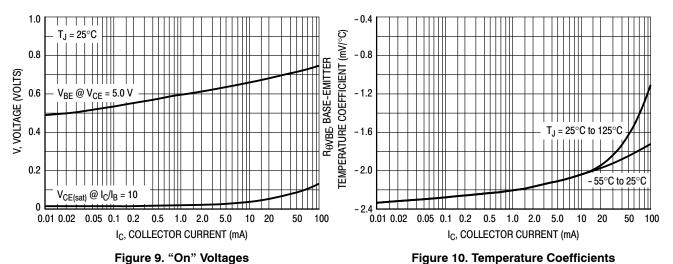


Figure 9. "On" Voltages

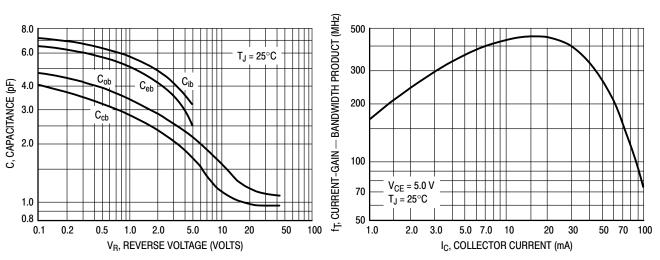


Figure 11. Capacitance

Figure 12. Current-Gain — Bandwidth Product

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

\_\_\_





#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

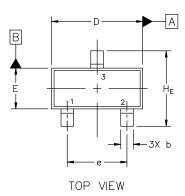
2.04

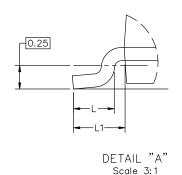
0.55

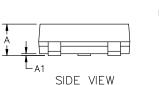
0.69

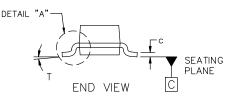
2.64

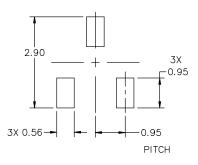
10°











#### NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package



\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 1 OF 2	

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries, onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

## SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODI	
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 2 OF 2	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales